



fastPACK E2 SiC

1200 V / 16 mΩ

Features

- Compact and low inductive design
- High frequency SiC MOSFET
- Integrated NTC

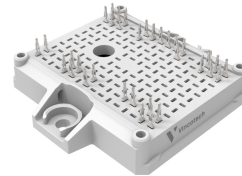
Target applications

- Charging Stations
- Power Supply
- Welding & Cutting

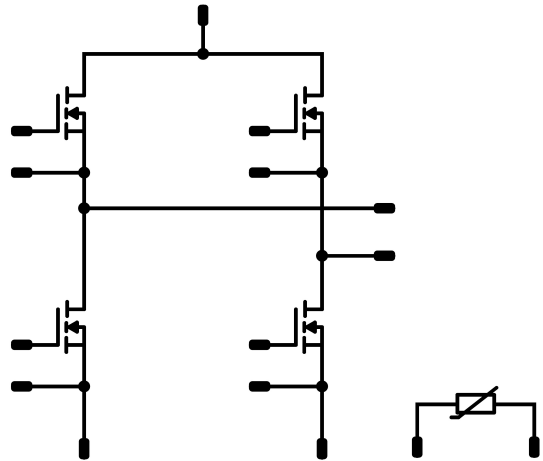
Types

- 10-EY124PA016ME-LP49F18T

flow E2 12 mm housing



Schematic



**Maximum Ratings** $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
H-Bridge Switch - Lo side				
Drain-source voltage	V_{DSS}		1200	V
Drain current	I_D	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	71	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}	240	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	126	W
Gate-source voltage	V_{GSS}		-4 / 15	V
Maximum Junction Temperature	T_{jmax}		175	°C

H-Bridge Switch - Hi side

Drain-source voltage	V_{DSS}		1200	V
Drain current	I_D	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	71	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}	240	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	126	W
Gate-source voltage	V_{GSS}		-4 / 15	V
Maximum Junction Temperature	T_{jmax}		175	°C

Module Properties**Thermal Properties**

Storage temperature	T_{stg}		-40...+125	°C
Operation temperature under switching condition	T_{jop}		-40...+($T_{jmax} - 25$)	°C

Isolation Properties

Isolation voltage	V_{isol}	DC Test Voltage* $t_p = 2\text{ s}$	6000	V
Isolation voltage	V'_{isol}	AC Voltage $t_p = 1\text{ min}$	2500	V
Creepage distance			min. 12,7	mm
Clearance			9,14	mm
Comparative Tracking Index	CTI		≥ 600	

*100 % tested in production



Vincotech

10-EY124PA016ME-LP49F18T
datasheet

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		

H-Bridge Switch - Lo side

Static

Drain-source on-state resistance	$r_{DS(on)}$		15		80	25 125 150	11,2	17 21 23	20,8	mΩ
Gate-source threshold voltage	$V_{GS(th)}$		0		0,02	25	1,8	2,5	3,6	V
Gate to Source Leakage Current	I_{GSS}		15	0		25		20	500	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	0	0	25		2	38	μA
Internal gate resistance	r_g							0,85		Ω
Gate charge	Q_g		-4/15	800	80	25		236		nC
Short-circuit input capacitance	C_{iss}	$f = 100$ kHz	0	1000	0	25		6714		pF
Short-circuit output capacitance	C_{oss}							258		
Reverse transfer capacitance	C_{rss}							16		
Diode forward voltage	V_{SD}		0		40	25		4,6		V

Thermal

Thermal resistance junction to sink*	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						0,75		K/W
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*Only valid with pre-applied Vincotech thermal interface material.

Dynamic

Turn-on delay time	$t_{d(on)}$	$R_{g(on)} = 2$ Ω $R_{g(off)} = 2$ Ω	-4/15	600	64	25		19,84		ns
Rise time	t_r					125		18,88		
						150		18,56		
						25		6,72		
Turn-off delay time	$t_{d(off)}$					125		6,4		
						150		6,4		
						25		42,24		
Fall time	t_f	125		44,8						
		150		45,76						
		25		9,4						
Turn-on energy (per pulse)	E_{on}	125		9,22						
		150		9,44						
		25		0,365						
Turn-off energy (per pulse)	E_{off}	125		0,35						
		150		0,366						
		25		0,125						
						125		0,118		mWs
						150		0,129		mWs



Vincotech

10-EY124PA016ME-LP49F18T
datasheet

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		

H-Bridge Switch - Hi side

Static

Drain-source on-state resistance	$r_{DS(on)}$		15		80	25 125 150	11,2	17 21 23	20,8	mΩ
Gate-source threshold voltage	$V_{GS(th)}$		0		0,02	25	1,8	2,5	3,6	V
Gate to Source Leakage Current	I_{GSS}		15	0		25		20	500	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	0	0	25		2	38	μA
Internal gate resistance	r_g							0,85		Ω
Gate charge	Q_g		-4/15	800	80	25		236		nC
Short-circuit input capacitance	C_{iss}	$f = 100$ kHz	0	1000	0	25		6714		pF
Short-circuit output capacitance	C_{oss}							258		
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Diode forward voltage	V_{SD}		0		40	25		4,6		V

Thermal

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Dynamic

Turn-on delay time	$t_{d(on)}$	$R_{g(on)} = 2$ Ω $R_{g(off)} = 2$ Ω	-4/15	600	64	25		19,84		ns
Rise time	t_r					125		18,88		
						150		18,56		
						25		6,72		
Turn-off delay time	$t_{d(off)}$					125		6,4		
						150		6,4		
						25		42,24		
Fall time	t_f	125		44,8						
		150		45,76						
		25		9,4						
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		150		9,44						
		25		0,365						
Turn-off energy (per pulse)	E_{off}	125		0,35						
		150		0,366						
		25		0,125						
						125		0,118		mWs
						150		0,129		



Vincotech

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GS} [V]	V_{GE} [V]	V_{DS} [V]	V_{CE} [V]	T_j [°C]	Min	Typ	Max	

Thermistor

Static

Rated resistance	R					25		5		kΩ
Deviation of R_{100}	$A_{R/R}$	$R_{100} = 493 \Omega$				100	-5		5	%
Power dissipation	P							245		mW
Power dissipation constant	d					25		1,4		mW/K
B-value	$B_{(25/50)}$	Tol. $\pm 2 \%$						3375		K
B-value	$B_{(25/100)}$	Tol. $\pm 2 \%$						3437		K
Vincotech Thermistor Reference									K	

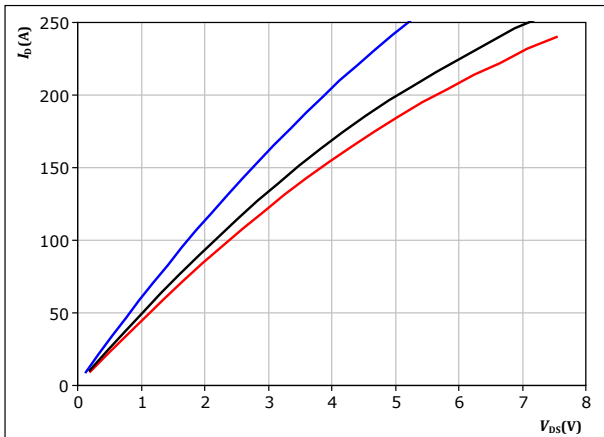


H-Bridge Switch - Lo side Characteristics

figure 1. MOSFET

Typical output characteristics

$$I_D = f(V_{DS})$$

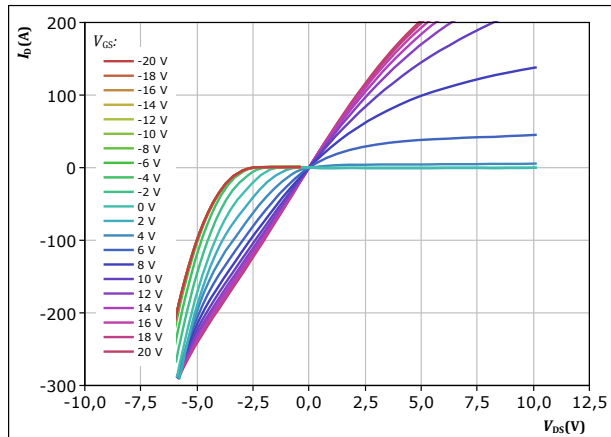


$t_p = 250 \mu s$
 $V_{GS} = 14 V$
 $T_j:$ — 25 °C
— 125 °C
— 150 °C

figure 2. MOSFET

Typical output characteristics

$$I_D = f(V_{DS})$$

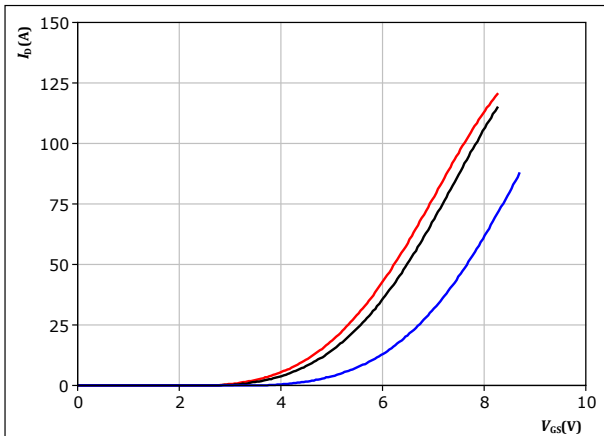


$t_p = 250 \mu s$
 $T_j = 150 \text{ } ^\circ\text{C}$
 V_{GS} from -20 V to 20 V in steps of 2 V

figure 3. MOSFET

Typical transfer characteristics

$$I_D = f(V_{GS})$$

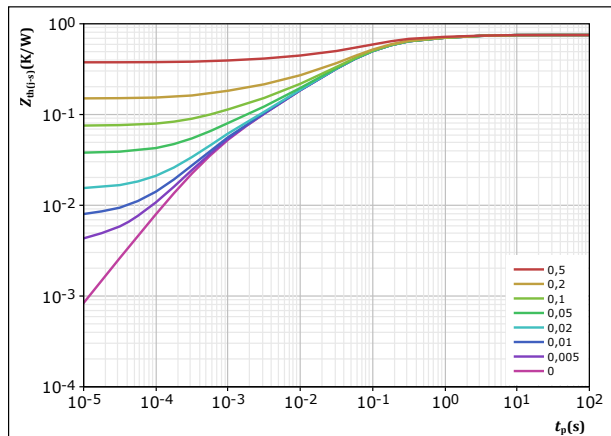


$t_p = 250 \mu s$
 $V_{DS} = 10 V$
 $T_j:$ — 25 °C
— 125 °C
— 150 °C

figure 4. MOSFET

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 0,752 \text{ K/W}$
IGBT thermal model values

R (K/W)	τ (s)
5,19E-02	2,61E+00
9,26E-02	5,45E-01
3,53E-01	9,51E-02
1,55E-01	2,37E-02
6,57E-02	3,84E-03
3,38E-02	5,95E-04

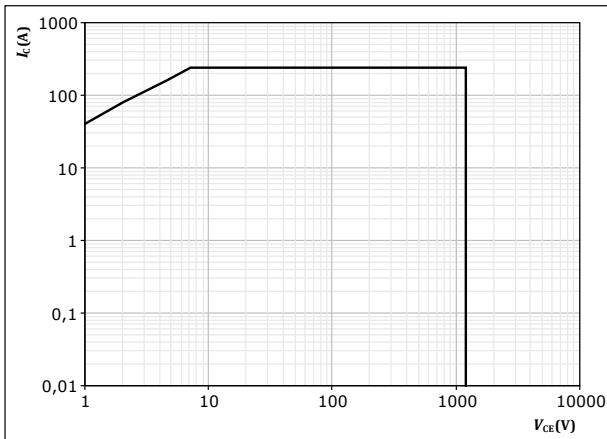


H-Bridge Switch - Lo side Characteristics

figure 5. MOSFET

Safe operating area

$$I_C = f(V_{CE})$$



$D =$ single pulse

$T_s = 80$ °C

$V_{GE} = 14$ V

$T_j = T_{jmax}$

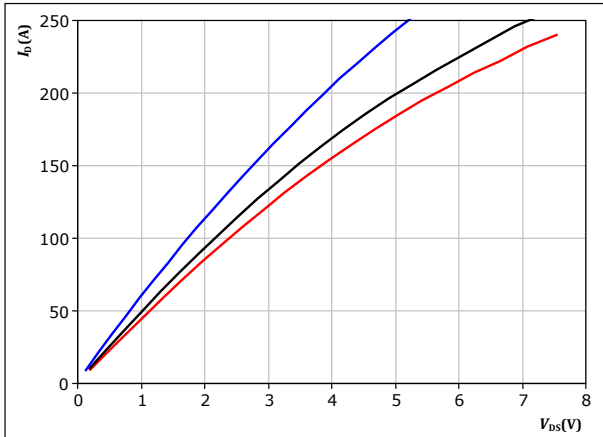


H-Bridge Switch - Hi side Characteristics

figure 6. MOSFET

Typical output characteristics

$$I_D = f(V_{DS})$$

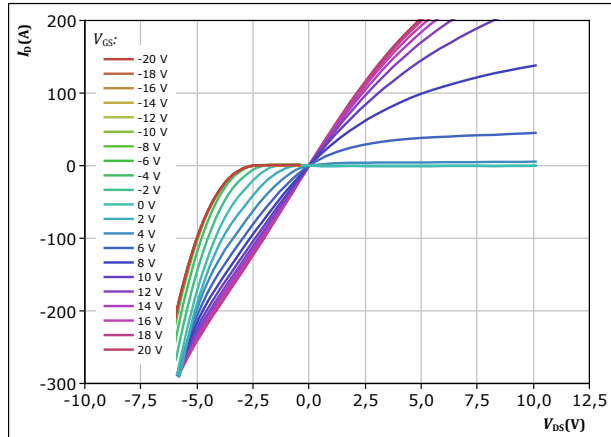


$t_p = 250 \mu s$
 $V_{GS} = 14 V$
 $T_j:$ — 25 °C
— 125 °C
— 150 °C

figure 7. MOSFET

Typical output characteristics

$$I_D = f(V_{DS})$$

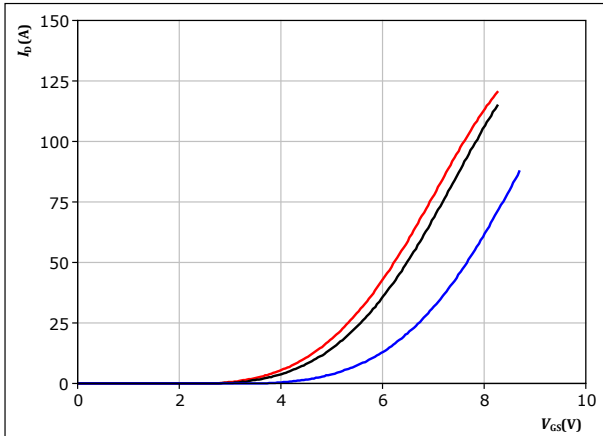


$t_p = 250 \mu s$
 $T_j = 150 \text{ } ^\circ C$
 V_{GS} from -20 V to 20 V in steps of 2 V

figure 8. MOSFET

Typical transfer characteristics

$$I_D = f(V_{GS})$$

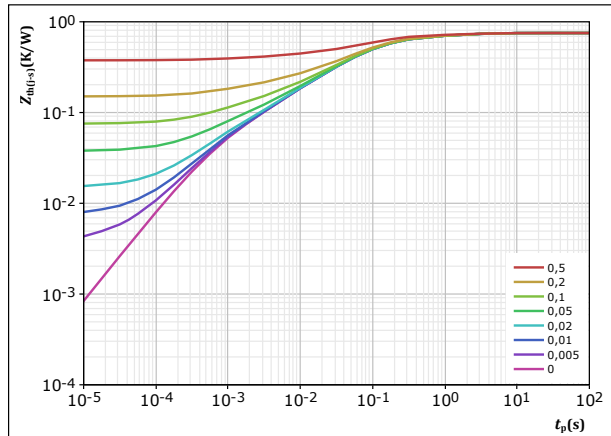


$t_p = 250 \mu s$
 $V_{DS} = 10 V$
 $T_j:$ — 25 °C
— 125 °C
— 150 °C

figure 9. MOSFET

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 0,752 \text{ K/W}$
IGBT thermal model values

R (K/W)	τ (s)
5,19E-02	2,61E+00
9,26E-02	5,45E-01
3,53E-01	9,51E-02
1,55E-01	2,37E-02
6,57E-02	3,84E-03
3,38E-02	5,95E-04

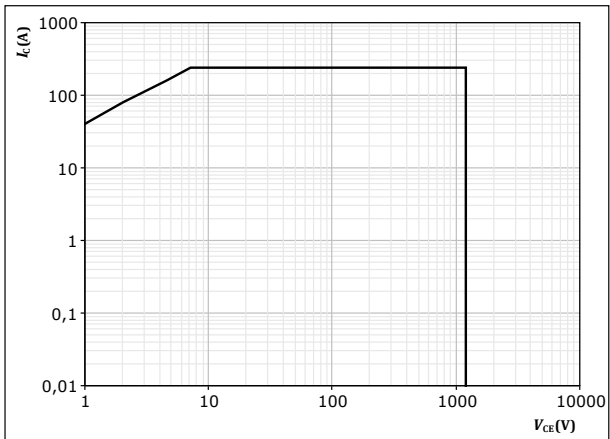


H-Bridge Switch - Hi side Characteristics

figure 10. MOSFET

Safe operating area

$$I_C = f(V_{CE})$$



$D =$ single pulse

$T_s = 80$ °C

$V_{GE} = 14$ V

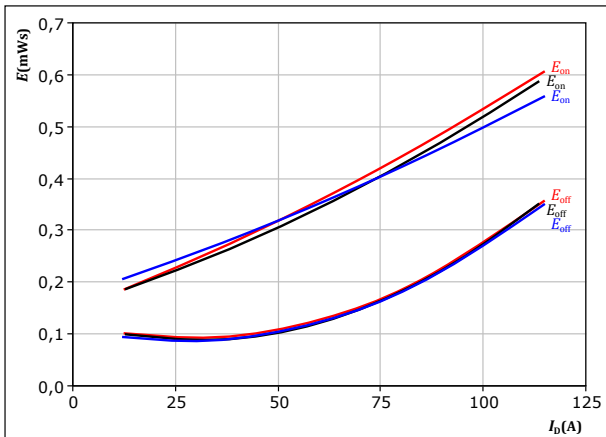
$T_j = T_{jmax}$



H-Bridge Switching Characteristics - Lo side

figure 11. MOSFET

Typical switching energy losses as a function of drain current
 $E = f(I_D)$

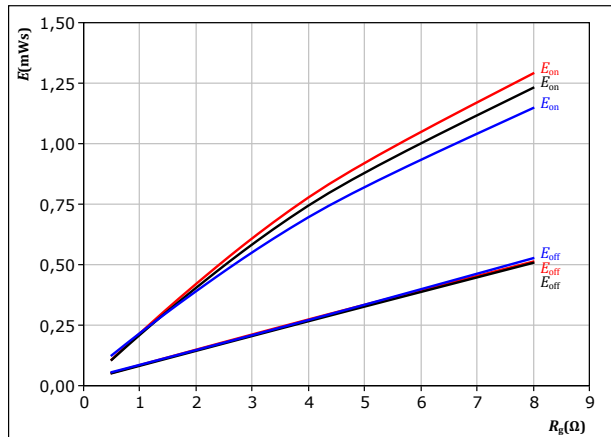


With an inductive load at

$V_{DS} =$	600	V	$T_j:$	25 °C
$V_{GS} =$	-4/15	V		125 °C
$R_{gon} =$	2	Ω		150 °C
$R_{goff} =$	2	Ω		

figure 12. MOSFET

Typical switching energy losses as a function of gate resistor
 $E = f(R_g)$

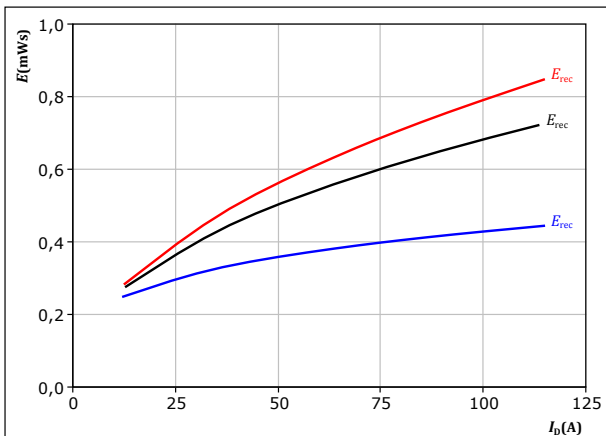


With an inductive load at

$V_{DS} =$	600	V	$T_j:$	25 °C
$V_{GS} =$	-4/15	V		125 °C
$I_D =$	64	A		150 °C

figure 13. MOSFET

Typical reverse recovered energy loss as a function of drain current
 $E_{rec} = f(I_D)$

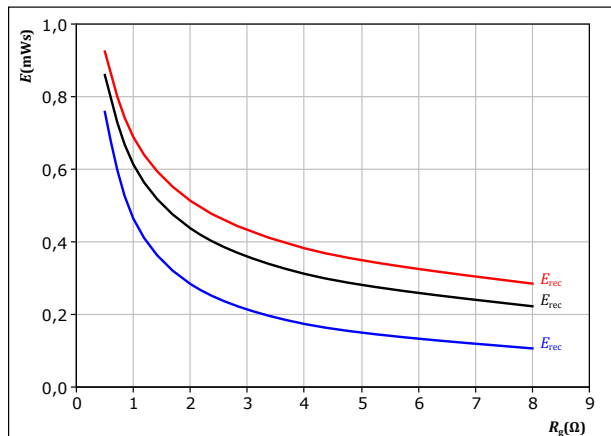


With an inductive load at

$V_{DS} =$	600	V	$T_j:$	25 °C
$V_{GS} =$	-4/15	V		125 °C
$R_{gon} =$	2	Ω		150 °C

figure 14. MOSFET

Typical reverse recovered energy loss as a function of gate resistor
 $E_{rec} = f(R_g)$



With an inductive load at

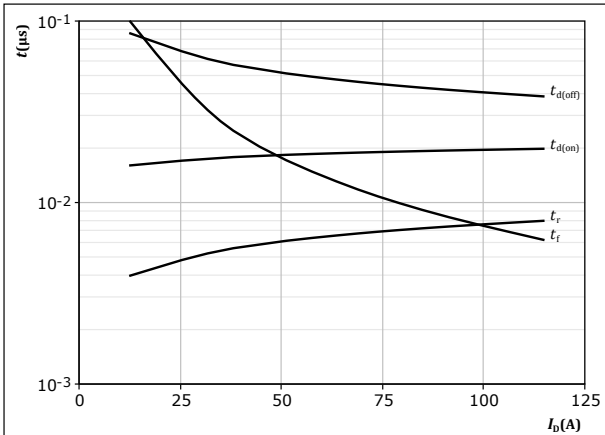
$V_{DS} =$	600	V	$T_j:$	25 °C
$V_{GS} =$	-4/15	V		125 °C
$I_D =$	64	A		150 °C



H-Bridge Switching Characteristics - Lo side

figure 15. MOSFET

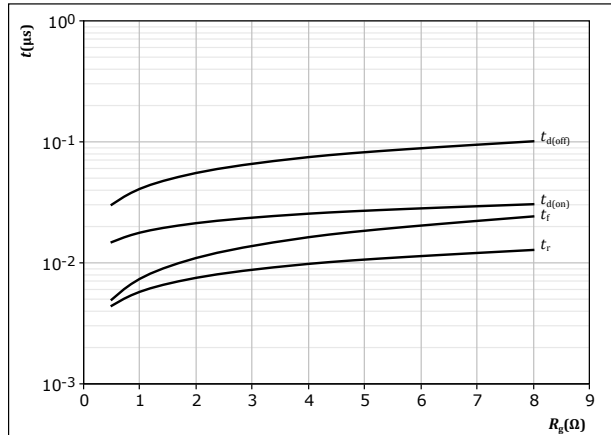
Typical switching times as a function of drain current
 $t = f(I_D)$



With an inductive load at
 $T_j = 150 \text{ } ^\circ\text{C}$
 $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $R_{gon} = 2 \text{ } \Omega$
 $R_{goff} = 2 \text{ } \Omega$

figure 16. MOSFET

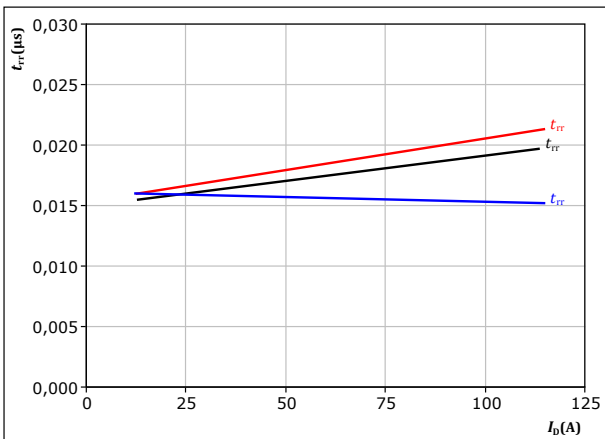
Typical switching times as a function of gate resistor
 $t = f(R_g)$



With an inductive load at
 $T_j = 150 \text{ } ^\circ\text{C}$
 $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $I_D = 64 \text{ A}$

figure 17. MOSFET

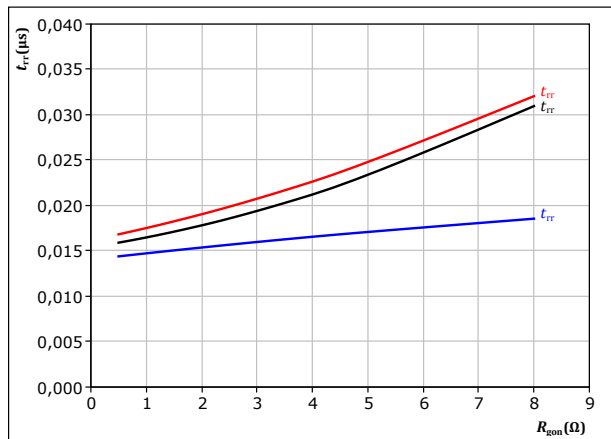
Typical reverse recovery time as a function of drain current
 $t_{rr} = f(I_D)$



At $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $R_{gon} = 2 \text{ } \Omega$
 T_j : — 25 °C
 — 125 °C
 — 150 °C

figure 18. MOSFET

Typical reverse recovery time as a function of turn on gate resistor
 $t_{rr} = f(R_{gon})$



At $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $I_D = 64 \text{ A}$
 T_j : — 25 °C
 — 125 °C
 — 150 °C

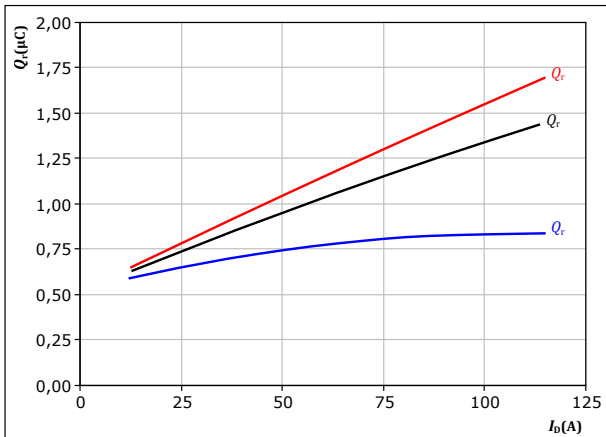


H-Bridge Switching Characteristics - Lo side

figure 19. MOSFET

Typical recovered charge as a function of drain current

$$Q_r = f(I_D)$$



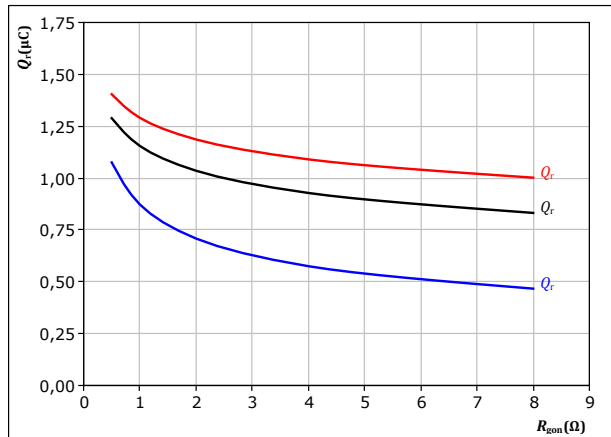
At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $R_{gson} = 2$ Ω

T_j : 25 °C (blue)
 125 °C (black)
 150 °C (red)

figure 20. MOSFET

Typical recovered charge as a function of turn on gate resistor

$$Q_r = f(R_{gson})$$



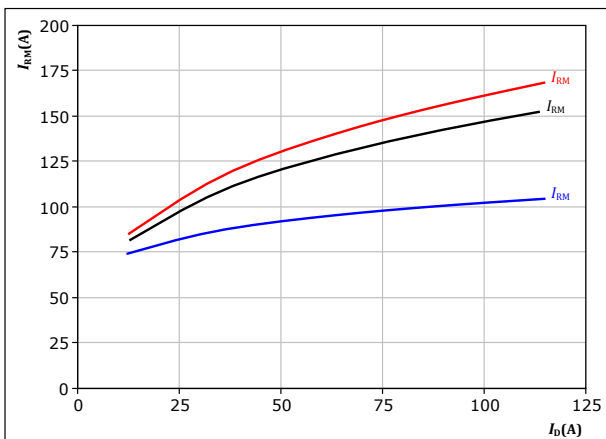
At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $I_D = 64$ A

T_j : 25 °C (blue)
 125 °C (black)
 150 °C (red)

figure 21. MOSFET

Typical peak reverse recovery current as a function of drain current

$$I_{RM} = f(I_D)$$



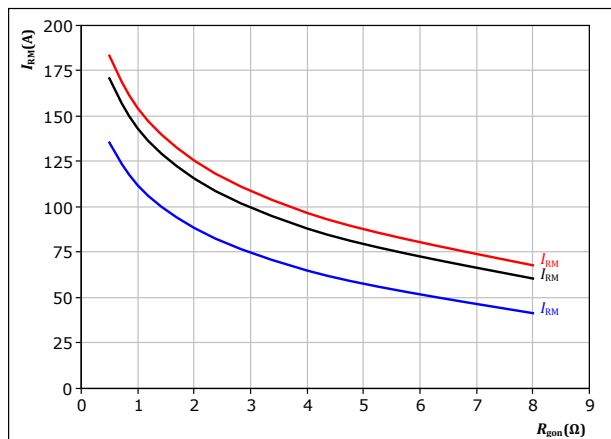
At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $R_{gson} = 2$ Ω

T_j : 25 °C (blue)
 125 °C (black)
 150 °C (red)

figure 22. MOSFET

Typical peak reverse recovery current as a function of turn on gate resistor

$$I_{RM} = f(R_{gson})$$



At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $I_D = 64$ A

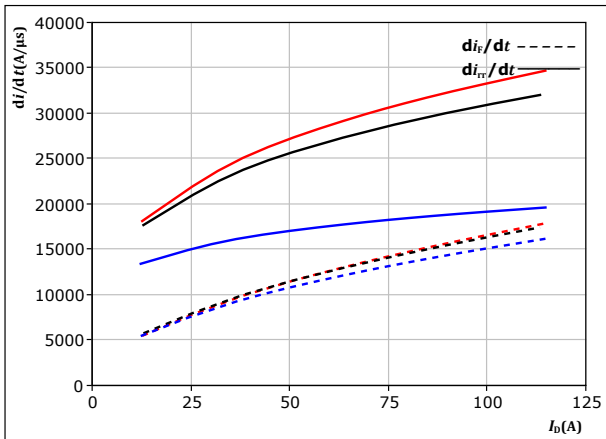
T_j : 25 °C (blue)
 125 °C (black)
 150 °C (red)



H-Bridge Switching Characteristics - Lo side

figure 23. MOSFET

Typical rate of fall of forward and reverse recovery current as a function of drain current
 $di_f/dt, di_{rr}/dt = f(I_D)$

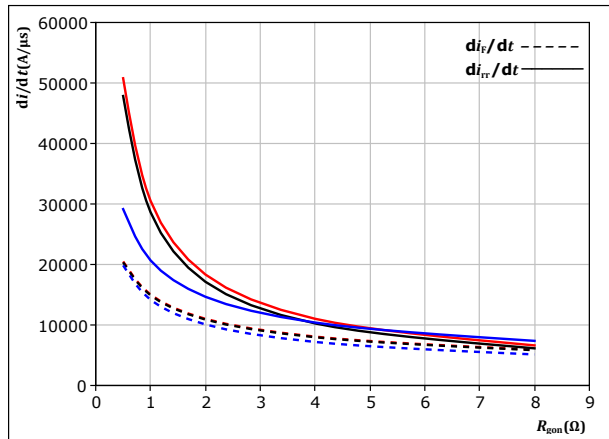


At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $R_{g(on)} = 2$ Ω

T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 24. MOSFET

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor
 $di_f/dt, di_{rr}/dt = f(R_{g(on)})$



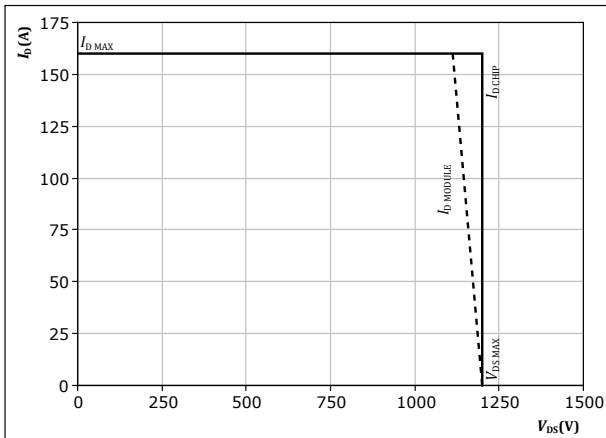
At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $I_D = 64$ A

T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 25. MOSFET

Reverse bias safe operating area

$I_D = f(V_{DS})$



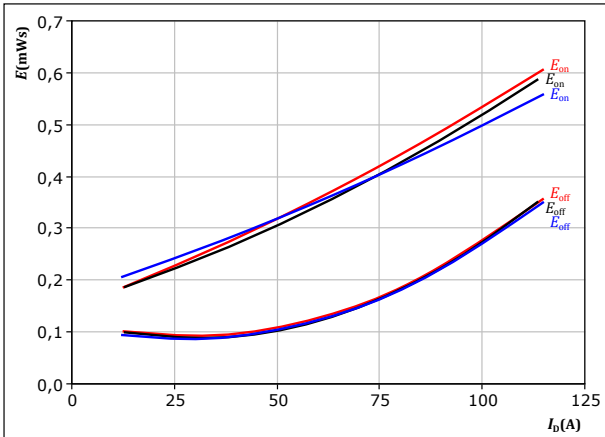
At $T_j = 150$ °C
 $R_{g(on)} = 2$ Ω
 $R_{g(off)} = 2$ Ω



H-Bridge Switching Characteristics - Hi side

figure 26. MOSFET

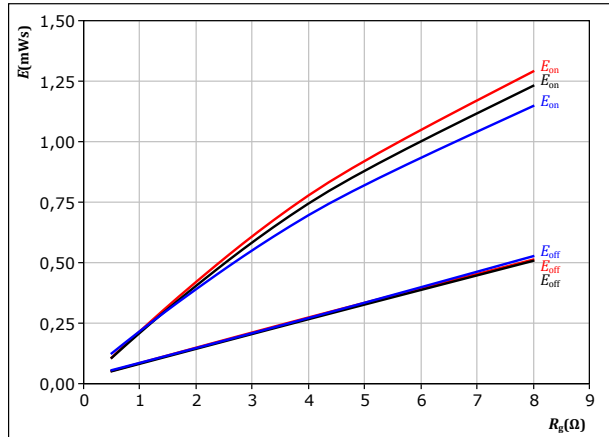
Typical switching energy losses as a function of drain current
 $E = f(I_D)$



With an inductive load at
 $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $R_{gon} = 2 \ \Omega$
 $R_{goff} = 2 \ \Omega$
 T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 27. MOSFET

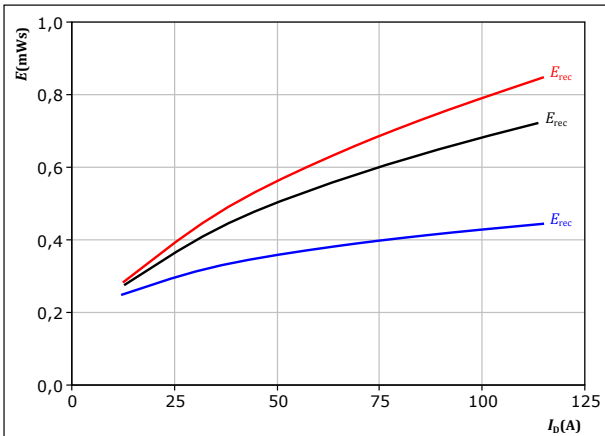
Typical switching energy losses as a function of gate resistor
 $E = f(R_g)$



With an inductive load at
 $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $I_D = 64 \text{ A}$
 T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 28. MOSFET

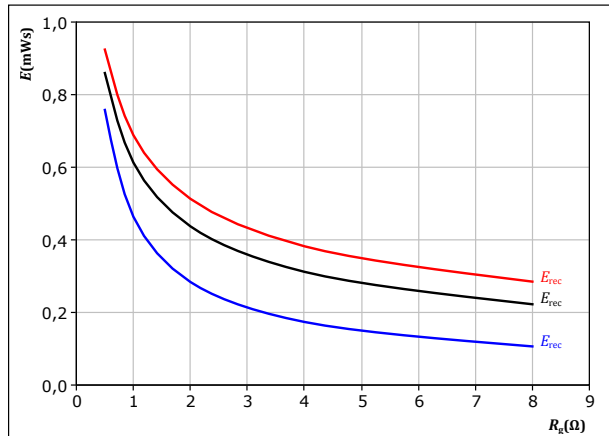
Typical reverse recovered energy loss as a function of drain current
 $E_{rec} = f(I_D)$



With an inductive load at
 $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $R_{gon} = 2 \ \Omega$
 T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 29. MOSFET

Typical reverse recovered energy loss as a function of gate resistor
 $E_{rec} = f(R_g)$



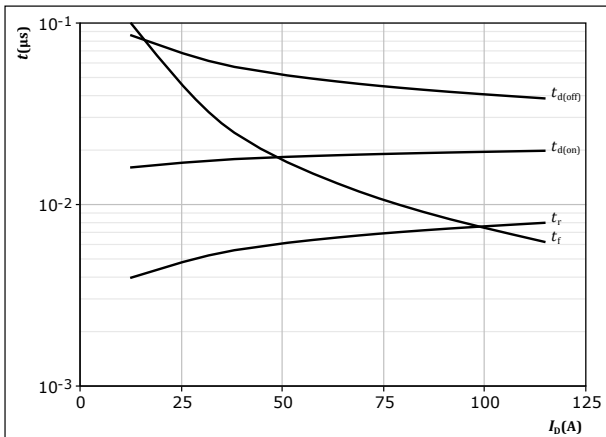
With an inductive load at
 $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $I_D = 64 \text{ A}$
 T_j : 25 °C (blue), 125 °C (black), 150 °C (red)



H-Bridge Switching Characteristics - Hi side

figure 30. MOSFET

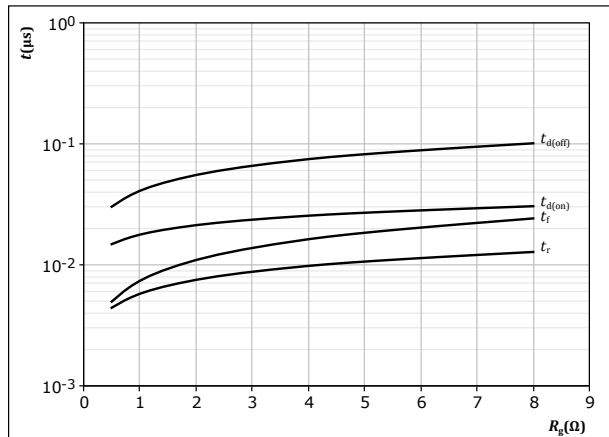
Typical switching times as a function of drain current
 $t = f(I_D)$



With an inductive load at
 $T_j = 150 \text{ }^\circ\text{C}$
 $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $R_{gon} = 2 \text{ } \Omega$
 $R_{goff} = 2 \text{ } \Omega$

figure 31. MOSFET

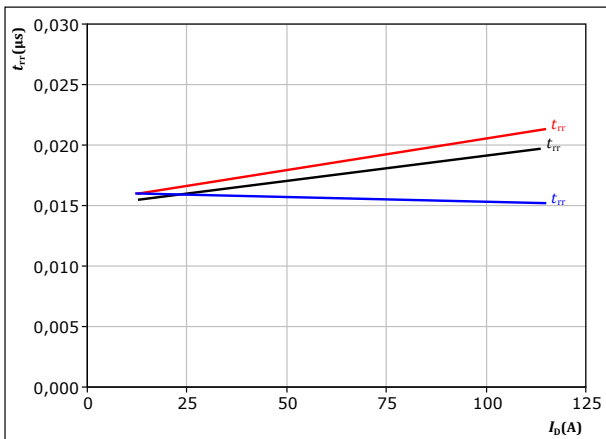
Typical switching times as a function of gate resistor
 $t = f(R_g)$



With an inductive load at
 $T_j = 150 \text{ }^\circ\text{C}$
 $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $I_D = 64 \text{ A}$

figure 32. MOSFET

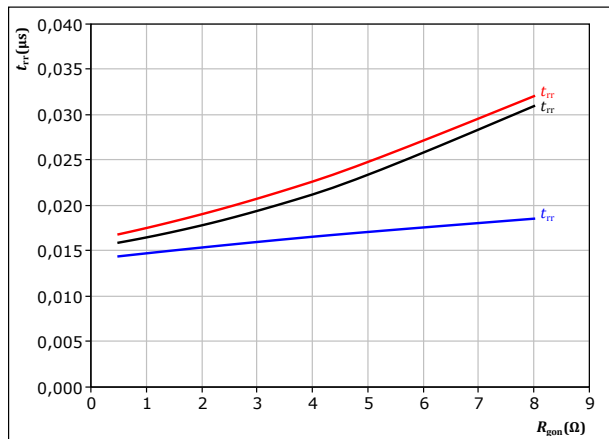
Typical reverse recovery time as a function of drain current
 $t_{rr} = f(I_D)$



At $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $R_{gon} = 2 \text{ } \Omega$
 T_j : — 25 °C
 — 125 °C
 — 150 °C

figure 33. MOSFET

Typical reverse recovery time as a function of turn on gate resistor
 $t_{rr} = f(R_{gon})$



At $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/15 \text{ V}$
 $I_D = 64 \text{ A}$
 T_j : — 25 °C
 — 125 °C
 — 150 °C

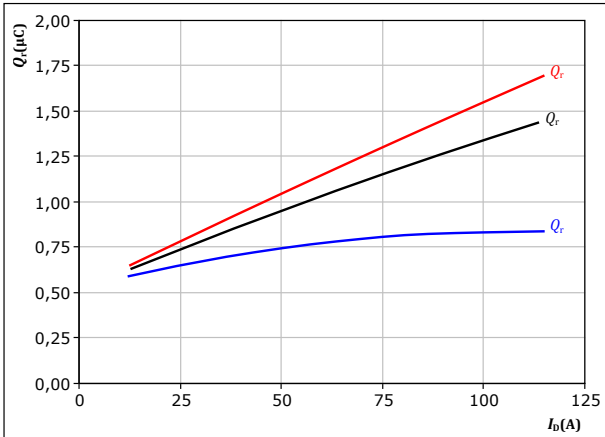


H-Bridge Switching Characteristics - Hi side

figure 34. MOSFET

Typical recovered charge as a function of drain current

$$Q_r = f(I_D)$$



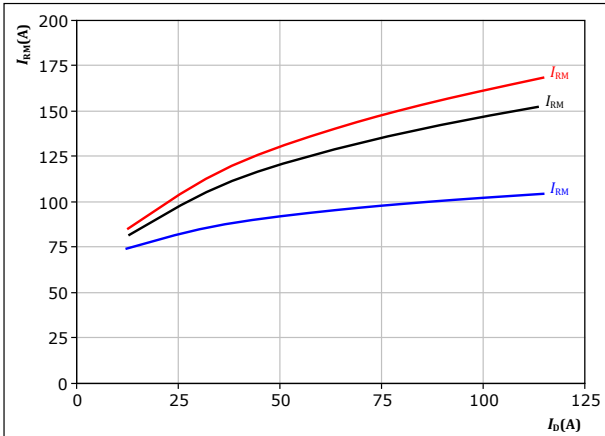
At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $R_{gon} = 2$ Ω

T_j : 25 °C (blue)
 125 °C (black)
 150 °C (red)

figure 36. MOSFET

Typical peak reverse recovery current as a function of drain current

$$I_{RM} = f(I_D)$$



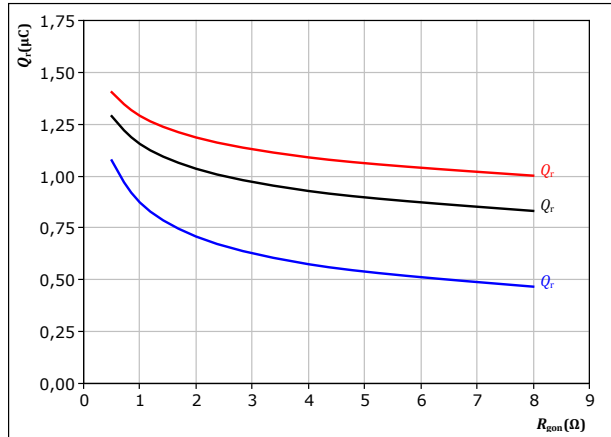
At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $R_{gon} = 2$ Ω

T_j : 25 °C (blue)
 125 °C (black)
 150 °C (red)

figure 35. MOSFET

Typical recovered charge as a function of turn on gate resistor

$$Q_r = f(R_{gon})$$



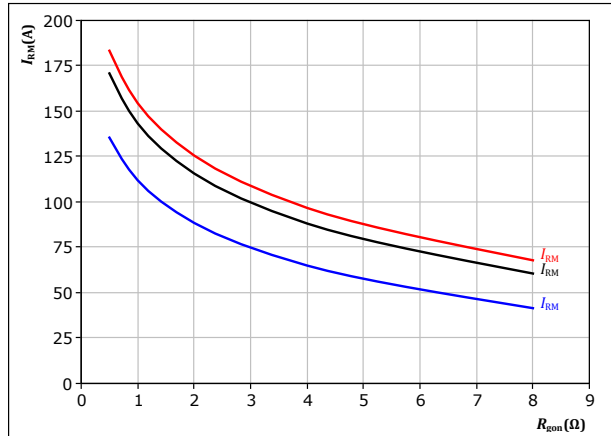
At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $I_D = 64$ A

T_j : 25 °C (blue)
 125 °C (black)
 150 °C (red)

figure 37. MOSFET

Typical peak reverse recovery current as a function of turn on gate resistor

$$I_{RM} = f(R_{gon})$$



At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $I_D = 64$ A

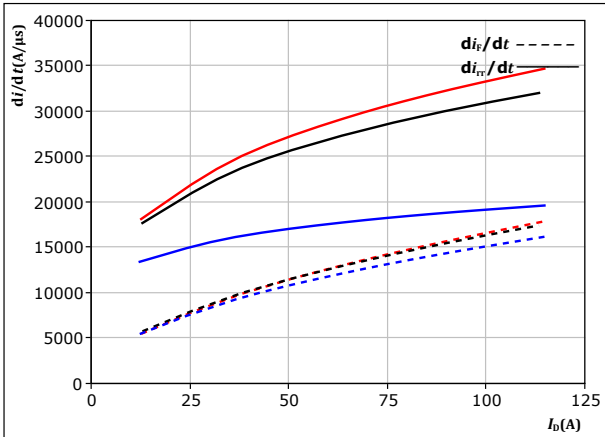
T_j : 25 °C (blue)
 125 °C (black)
 150 °C (red)



H-Bridge Switching Characteristics - Hi side

figure 38. MOSFET

Typical rate of fall of forward and reverse recovery current as a function of drain current
 $di_f/dt, di_{rr}/dt = f(I_D)$

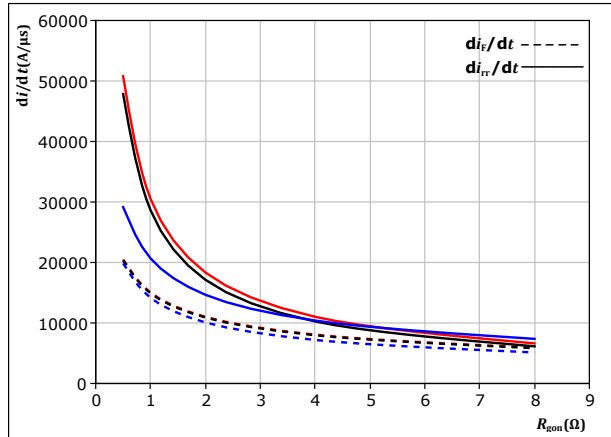


At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $R_{g(on)} = 2$ Ω

T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 39. MOSFET

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor
 $di_f/dt, di_{rr}/dt = f(R_{g(on)})$



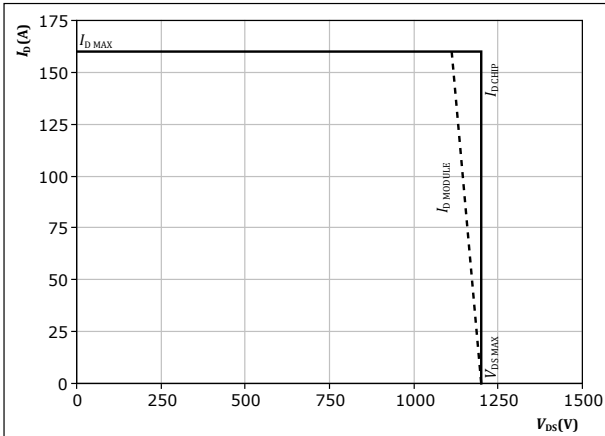
At $V_{DS} = 600$ V
 $V_{GS} = -4/15$ V
 $I_D = 64$ A

T_j : 25 °C (blue), 125 °C (black), 150 °C (red)

figure 40. MOSFET

Reverse bias safe operating area

$I_D = f(V_{DS})$



At $T_j = 150$ °C
 $R_{g(on)} = 2$ Ω
 $R_{g(off)} = 2$ Ω



Switching Definitions

figure 41. MOSFET

Turn-off Switching Waveforms & definition of t_{doff} t_{Eoff} (t_{Eoff} = integrating time for E_{off})

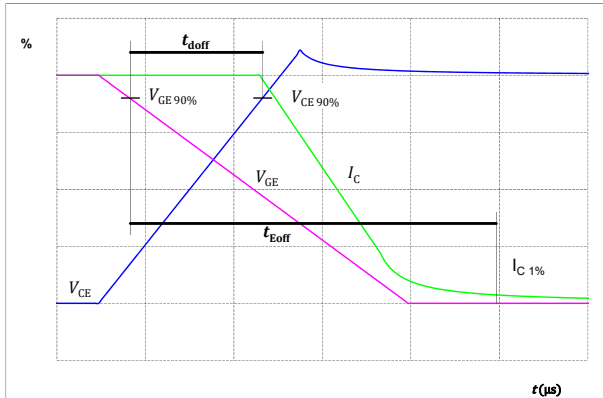


figure 42. MOSFET

Turn-on Switching Waveforms & definition of t_{don} t_{Eon} (t_{Eon} = integrating time for E_{on})

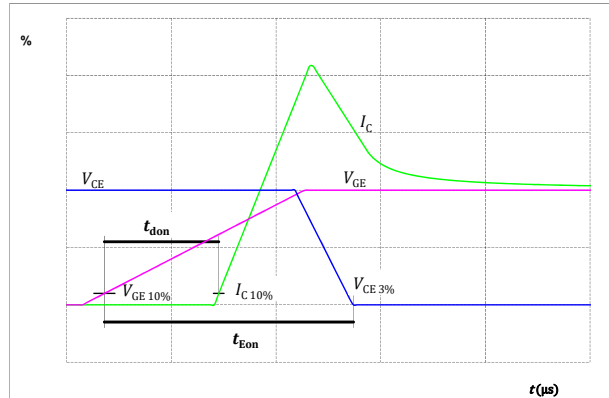


figure 43. MOSFET

Turn-off Switching Waveforms & definition of t_f

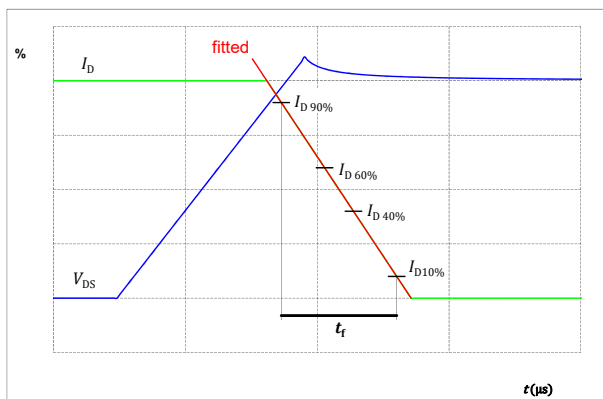
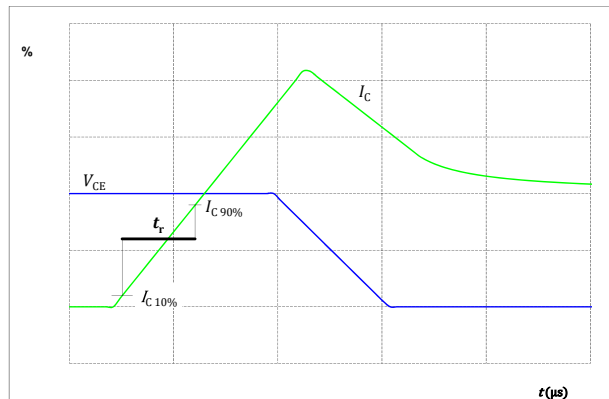


figure 44. MOSFET

Turn-on Switching Waveforms & definition of t_r





Switching Definitions

figure 45. FWD

Turn-off Switching Waveforms & definition of t_{tr}

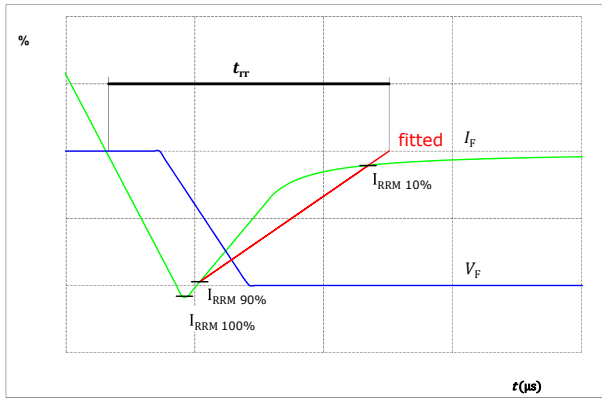


figure 46. FWD

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)

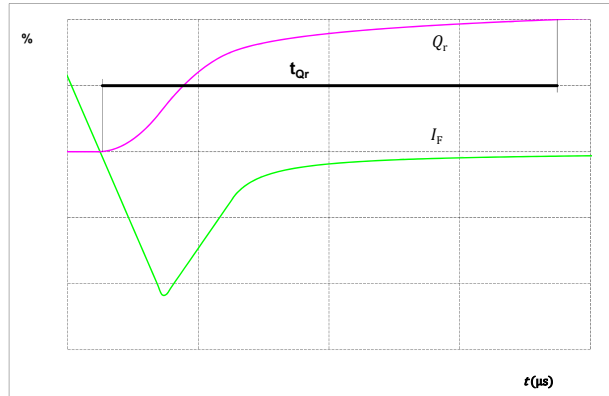
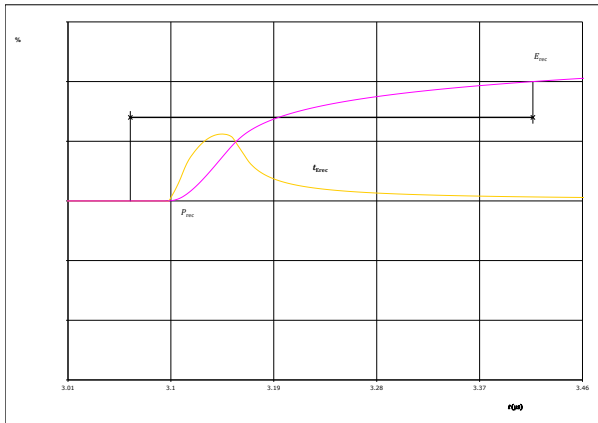


figure 47. FWD

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})






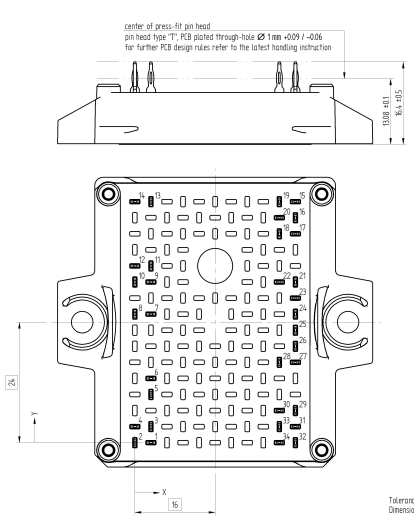
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10-EY124PA016ME-LP49F18T
datasheet

Ordering Code	
Version	Ordering Code
Without thermal paste	10-EY124PA016ME-LP49F18T
With thermal paste	10-EY124PA016ME-LP49F18T-/3/

Marking						
	Text	Name NN-NNNNNNNNNNNNNN- TTTTTVV	Date code WWYY	UL & VIN UL VIN	Lot LLLLL	Serial SSSS
	Datamatrix	Type&Ver TTTTTTTV	Lot number LLLLL	Serial SSSS	Date code WWYY	

Pin table [mm]			
Pin	X	Y	Function
1	3,2	0	AC2
2	0	0	AC2
3	3,2	3,2	AC2
4	0	3,2	AC2
5	3,2	9,6	S3
6	3,2	12,8	G3
7	3,2	25,6	S1
8	0	25,6	G1
9	3,2	32	AC1
10	0	32	AC1
11	3,2	35,2	AC1
12	0	35,2	AC1
13	3,2	48	T1
14	0	48	T2
15	32	48	DC-1
16	32	44,8	DC-1
17	32	41,6	DC-1
18	28,8	41,6	DC-1
19	28,8	48	G2
20	28,8	44,8	S2
21	32	32	DC+
22	28,8	32	DC+
23	32	28,8	DC+
24	32	25,6	DC+
25	32	22,4	DC+
26	32	19,2	DC+
27	32	16	DC+
28	28,8	16	DC+
29	32	6,4	DC-2
30	28,8	6,4	DC-2
31	32	3,2	DC-2
32	32	0	DC-2
33	28,8	3,2	S4
34	28,8	0	G4

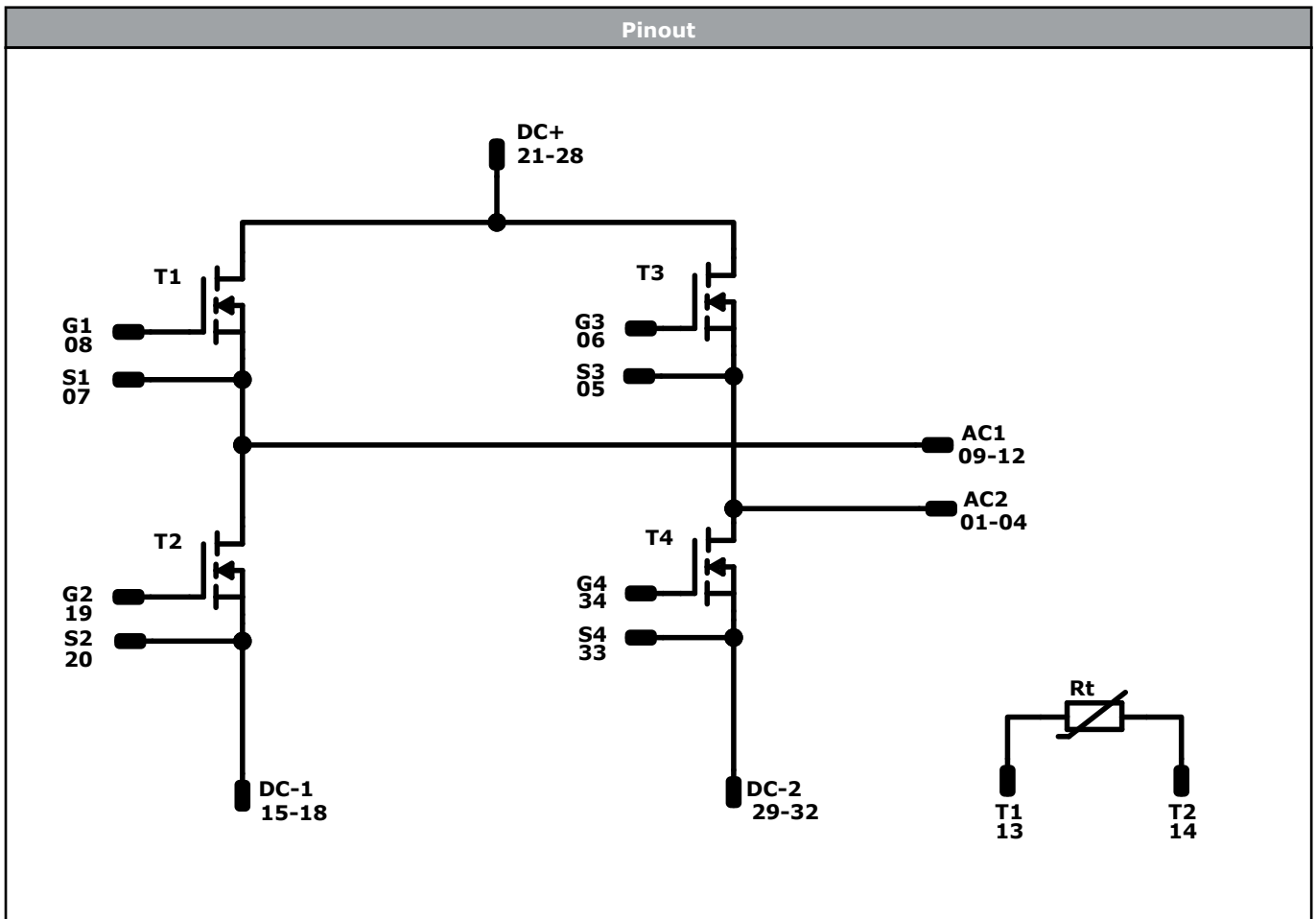


center of press-fit pin head
pin head type "1", PCB plated through-hole $\varnothing 1\text{mm} \pm 0,09\text{mm}$
for further PCB design rules refer to the latest handling instruction

Tolerance of pinposition: $\pm 0,4\text{mm}$ at the end of pins
Dimension of coordinate axis is only offset without tolerance



Vincotech




Identification					
ID	Component	Voltage	Current	Function	Comment
T2, T4	MOSFET	1200 V	16 mΩ	H-Bridge Switch - Lo side	
T1, T3	MOSFET	1200 V	16 mΩ	H-Bridge Switch - Hi side	
Rt	Thermistor			Thermistor	



Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for <i>flow</i> E2 packages see vincotech.com website.

Package data
Package data for <i>flow</i> E2 packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website. 

Document No.:	Date:	Modification:	Pages
10-EY124PA016ME-LP49F18T-D1-14	31 Mar. 2020		

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.